

Description

The RZE002P02TL uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

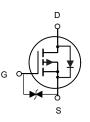
 $V_{DS} = -20V I_D = -0.66A$ $R_{DS(ON)} < 560 m\Omega@ V_{GS} = -4.5V$ $R_{DS(ON)} < 780 m\Omega@ V_{GS} = -2.5V$ ESD Rating: 1500V HBM

Application

Battery protection Load switch Uninterruptible power supply







P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)	
RZE002P02TL	SOT-523	HXY MOSFET	3000	

Absolute Maximum Ratings (T_A=25[°]C unless otherwise noted)

Symbol	Symbol Parameter		Unit	
V _{DS}	Drain-Source Voltage	-20	V	
Vgs	Gate-Source Voltage	±12	V	
ID	Drain Current-Continuous	-0.66	A	
P _D	Maximum Power Dissipation 1		mW	
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C	
Reja	R _{0JA} Thermal Resistance, Junction-to-Ambient (Note 2)		°C/W	
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	833		



Symbol	Test conditions	Min	Тур	Max	Unit
STATIC CHARACTERISTICE					
V _{(BR)DSS}	V _{GS} = 0V, I _D =-250µA	-20			V
I _{DSS}	V _{DS} =-20V,V _{GS} = 0V			-1	μA
lgss	$V_{GS} = \pm 10 V$, $V_{DS} = 0 V$			±10	μA
V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250µA	-0.4	-0.7	-1.0	V
R _{DS(on)}	V _{GS} =-4.5V, I _D =-0.5A			0.56	Ω
	V _{GS} =-2.5V, I _D =-0.2A			0.78	Ω
Is				-0.6	А
lsм				-1.2	A
V _{SD}	I _S =-0.5A, V _{GS} = 0V			-1.2	V
DYNAMIC CHARACTERISTICS (note4)					
C _{iss}			115		pF
Coss			15		pF
C _{rss}			9		pF
te4)					
t _{d(on)}			9		nS
tr	V _{GS} =-4.5V,V _{DS} =-10V,		6		nS
t _{d(off)}	I_D =-200mA,R _{GEN} =10 Ω		33		nS
t _f			22		nS
	V(BR)DSS IDSS IGSS VGS(th) RDS(on) IS ISM VSD Ciss Coss Crss te4) td(on) tr td(off)	$\begin{tabular}{ c c c c } \hline V_{(BR)DSS} & V_{GS} = 0V, I_D =-250 \mu A \\ \hline I_{DSS} & V_{DS} =-20V, V_{GS} = 0V \\ \hline I_{GSS} & V_{GS} =\pm 10V, V_{DS} = 0V \\ \hline V_{GS(th)} & V_{DS} = V_{GS}, I_D =-250 \mu A \\ \hline V_{GS} =-4.5V, I_D =-0.5A \\ \hline V_{GS} =-2.5V, I_D =-0.2A \\ \hline I_S & \\ \hline I_{SM} & \\ \hline V_{SD} & I_S =-2.5V, I_D =-0.2A \\ \hline I_S & \\ \hline V_{SD} & I_S =-2.5V, I_D =-0.2A \\ \hline I_S & \\ \hline V_{SD} & I_S =-2.5V, I_D =-0.2A \\ \hline I_S & \\ \hline V_{SD} & I_S =-2.5V, I_D =-0.2A \\ \hline I_S & \\ \hline V_{SD} & I_S =-2.5V, I_D =-0.2A \\ \hline I_S & \\ \hline V_{SD} & I_S =-2.5V, I_D =-0.2A \\ \hline I_S & \\ \hline V_{SD} & I_S =-2.5V, I_D =-0.2A \\ \hline I_S & \\ \hline V_{SD} & I_S =-2.5V, I_D =-0.2A \\ \hline I_S & \\ \hline V_{SD} & I_S =-2.5V, I_D =-0.2A \\ \hline I_S & \\ \hline V_{SD} & I_S =-2.5V, I_D =-0.2A \\ \hline I_S & \\ \hline V_{SD} & I_S =-2.5V, I_D =-0.2A \\ \hline I_S & \\ \hline V_{SD} & I_S =-2.5V, I_D =-0.2A \\ \hline I_S & \\ \hline V_{SD} & I_S =-2.5V, I_D =-0.2A \\ \hline I_S & \\ \hline V_{SD} & I_S =-2.5V, I_D =-0.2A \\ \hline I_S & \\ \hline V_{SD} & I_S =-2.5V, I_D =-0.2A \\ \hline I_S & \\ \hline V_{SD} & I_S =-0.5A, V_{GS} = 0V \\ \hline V_{SD} & I_S =-0.5A, V_{GS} = 0V \\ \hline I_S & \\ \hline V_{SD} & I_S =-2.5V, V_{DS} =-10V, \\ \hline I_D =-200mA, R_{GEN} =10\Omega \\ \hline I_S & I_S =-2.5V, V_{DS} =-10V, \\ \hline I_D =-200mA, R_{GEN} =10\Omega \\ \hline I_S & I_S =-2.5V, V_{SD} =-10V, \\ \hline I_S =-200mA, R_{GEN} =10\Omega \\ \hline I_S & I_S =-2.5V, V_{SD} =-10V, \\ \hline I_S =-200mA, R_{GEN} =10\Omega \\ \hline I_S & I_S =-2.5V, V_{SD} =-10V, \\ \hline I_S & I_S =-2.5V, V_{DS} =-10V, \\ \hline I_S & I_S =-2.5V, V_{SD} =-10V, \\ \hline I_S & I_S =-2.5$	$\begin{tabular}{ c c c c c } \hline V_{(BR)DSS} & V_{GS} = 0V, I_D = -250 \mu A & -20 \\ \hline I_{DSS} & V_{DS} = -20V, V_{GS} = 0V & & & & \\ \hline I_{GSS} & V_{GS} = \pm 10V, V_{DS} = 0V & & & & \\ \hline V_{GS}(th) & V_{DS} = V_{GS}, I_D = -250 \mu A & -0.4 & & \\ \hline V_{GS}(th) & V_{DS} = V_{GS}, I_D = -0.5A & & & & \\ \hline V_{GS} = -2.5V, I_D = -0.2A & & & & \\ \hline I_{S} & & & & & & \\ \hline I_{S} & & & & & & \\ \hline I_{SM} & & & & & & \\ \hline I_{SM} & & & & & & \\ \hline V_{SD} & I_S = -0.5A, V_{GS} = 0V & & & & \\ \hline \hline V_{SD} & I_S = -0.5A, V_{GS} = 0V & & & \\ \hline \hline \hline \hline C_{iss} & & & & \\ \hline V_{DS} = -16V, V_{GS} = 0V, & & & \\ \hline \hline \hline C_{irss} & & & & \\ \hline I_{Cirss} & & & & \\ \hline \hline I_{c4(off)} & & & & \\ \hline V_{GS} = -4.5V, V_{DS} = -10V, & & & \\ \hline I_{c1} = -200 mA, R_{GEN} = 10\Omega & & & \\ \hline \hline$	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $

Electrical Characteristics (TJ=25°C, unless otherwise noted)

Notes:

1. Surface mounted on FR4 board using the minimum recommended pad size.

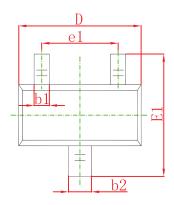
2. Pulse Test : Pulse Width=300µs, Duty Cycle=2%.

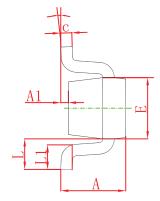
3. Switching characteristics are independent of operating junction temperatures.

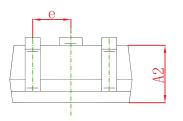
4. Guaranteed by design, not subject to producting.



SOT-523 Package Information

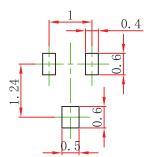






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	0.700	0.900	0.028	0.035	
A1	0.000	0.100	0.000	0.004	
A2	0.700	0.800	0.028	0.031	
b1	0.150	0.250	0.006	0.010	
b2	0.250	0.350	0.010	0.014	
С	0.100	0.200	0.004	0.008	
D	1.500	1.700	0.059	0.067	
E	0.700	0.900	0.028	0.035	
E1	1.450	1.750	0.057	0.069	
е	0.500 TYP.		0.020 TYP.		
e1	0.900	1.100	0.035	0.043	
L	0.400 REF.		0.016	0.016 REF.	
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

SOT-523 Suggested Pad Layout



Note:

1.Controlling dimension:in millimeters.

2.General tolerance:±0.05mm.

3. The pad layout is for reference purposes only.



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